TM90N02D

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

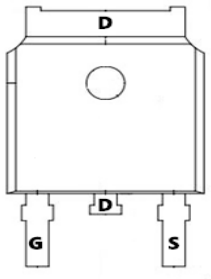
General Features

V_{DS} =20V I_D =90A

$R_{DS(ON)}$=3.4mΩ(typ.)@V_{GS}=4.5V

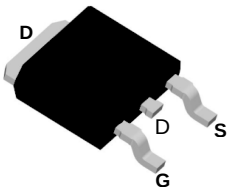
100% UIS Tested

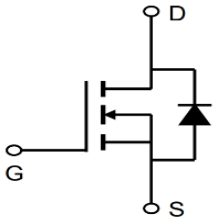
100% R_g Tested



Marking: 90N02

D:TO-252-3L





Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ 10V[1]	90	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ 10V[1]	35	A
I_{DM}	Pulsed Drain Current[2]	200	A
EAS	Single Pulse Avalanche Energy[3]	58	mJ
I_{AS}	Avalanche Current	41	A
P_D@T_C=25°C	Total Power Dissipation[4]	58	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R	Thermal Resistance Junction Case[1]		2 6	°C/W

© 2018 Tritech-MOS Technology Corporation

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.4	0.7	1.1	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=4.5V, I_D=30A		3.4	5	mΩ
		V_{GS}=2.5V, I_D=20A	-	4.75	6.5	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=10V, V_{GS}=0V, f = 1.0MHz	-	2500	-	pF
C_{oss}	Output Capacitance		-	407	-	pF
C_{rss}	Reverse Transfer Capacitance		-	386	-	pF
Q_g	Total Gate Charge	V_{DS}=10V, I_D=30A, V_{GS}=4.5V	-	32	-	nC
Q_{gs}	Gate-Source Charge		-	3	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	11	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=10V, I_D=30A, R_{GEN}=3Ω, V_{GS} =4.5V	-	17	-	ns
t_r	Turn-on Rise Time		-	49	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	74	-	ns
t_f	Turn-off Fall Time		-	26	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	90	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S=30A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25℃, V_{DD}=10V, V_G=4.5V, L=0.5mH, R_G=25Ω, I_{AS}=15A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

© 2018 Tritech-MOS Technology Corporation

Typical Performance Characteristics

Figure1: Output Characteristics

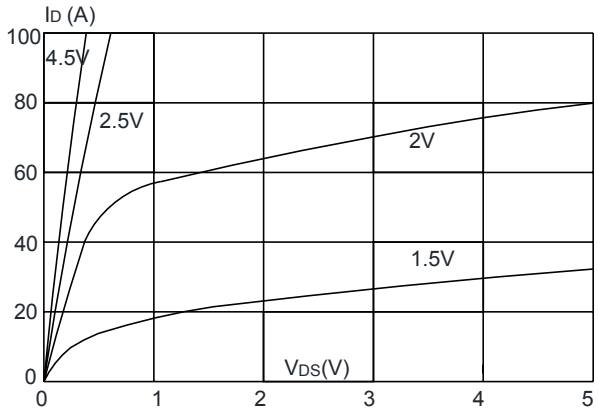


Figure 2: Typical Transfer Characteristics

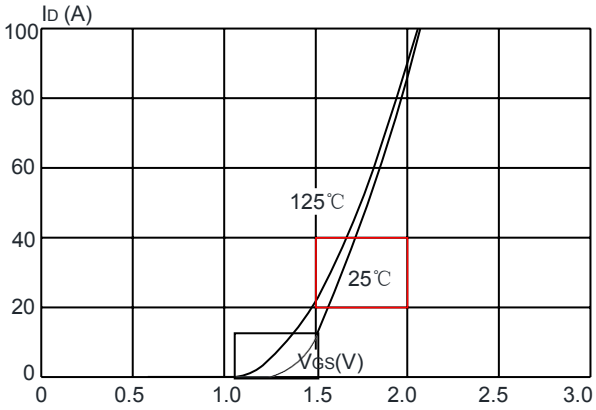


Figure 3: On-resistance vs. Drain Current

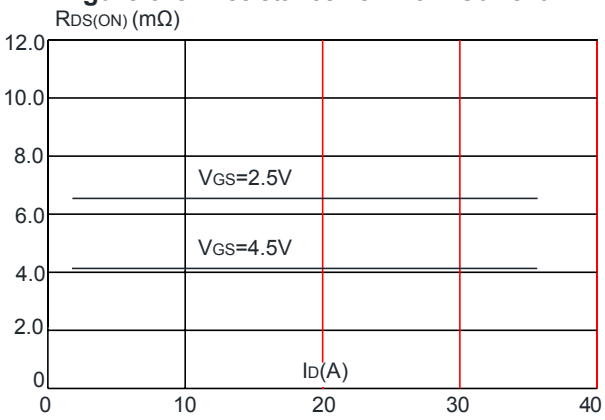


Figure 4: Body Diode Characteristics

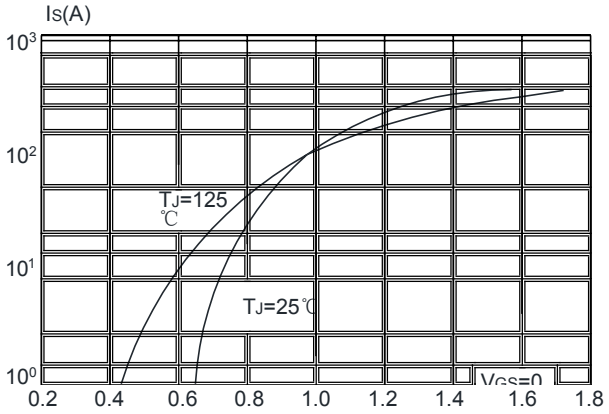


Figure 5: Gate Charge Characteristics

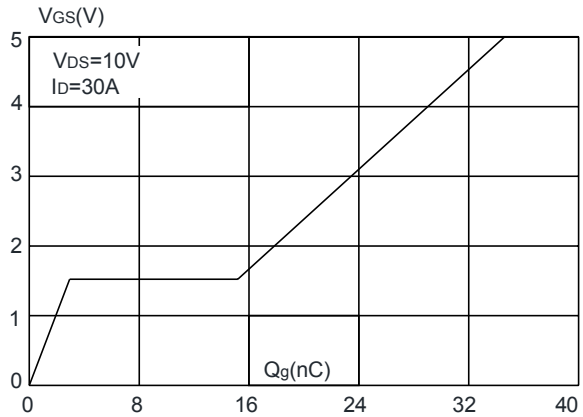
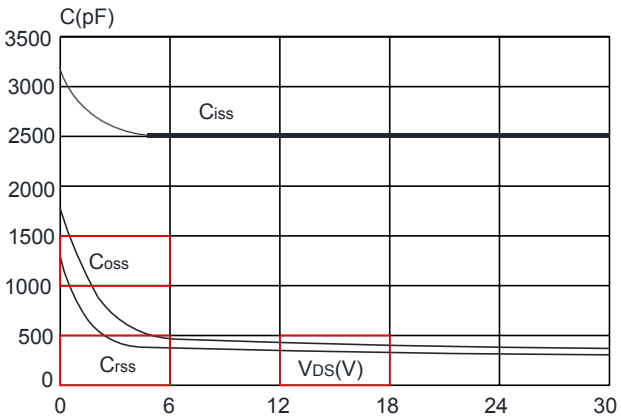


Figure 6: Capacitance Characteristics



© 2018 Tritech-MOS Technology Corporation

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

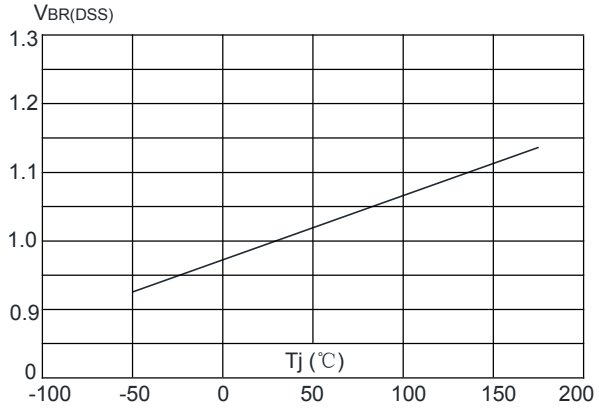


Figure 8: Normalized on Resistance vs. Junction Temperature

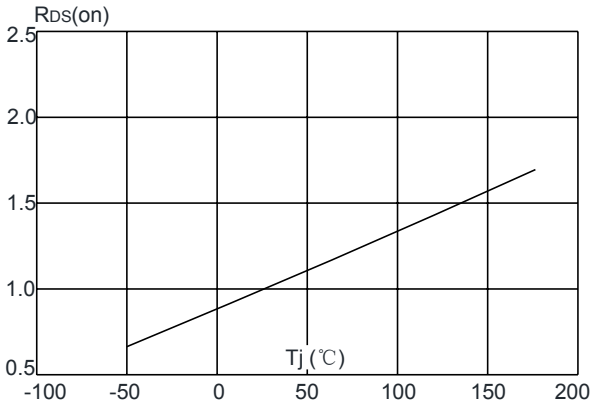


Figure 9: Maximum Safe Operating Area

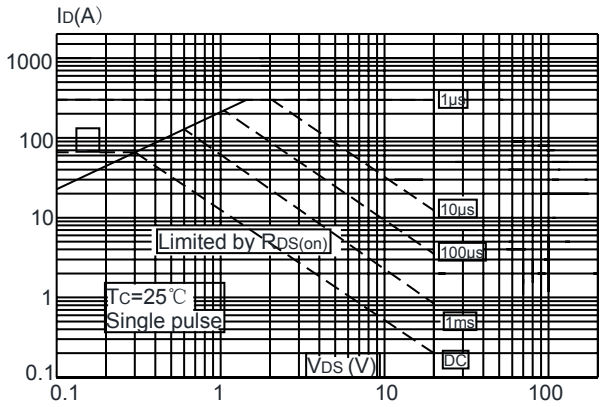


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

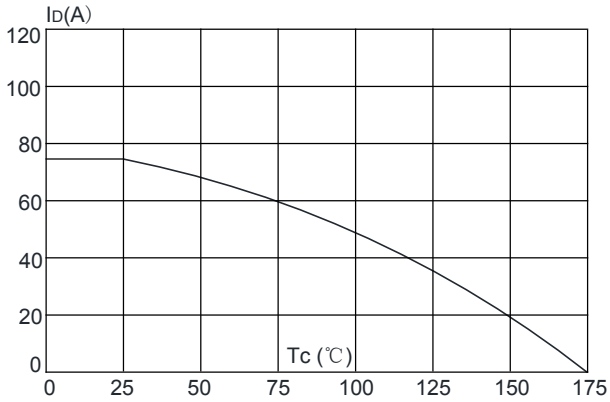
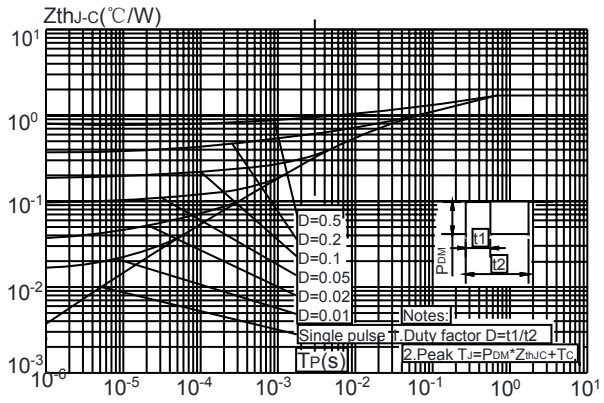
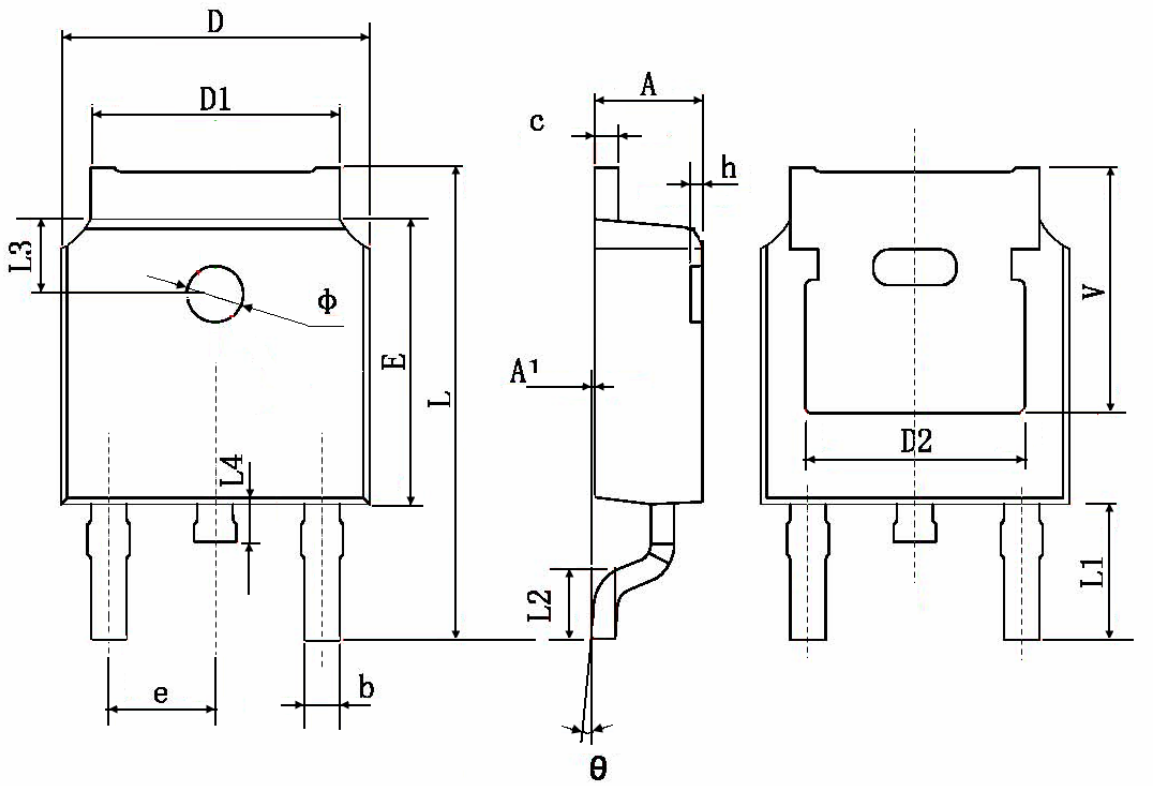


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



© 2018 Tritech-MOS Technology Corporation

Package Information:TO-252-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

© 2018 Tritech-MOS Technology Corporation